

SEMISTACK

Antiparallel thyristors for softstart

SKKQ 350

Features

- · Compact design
- · Thyristor with amplifying gate
- Pressure contact technology

Typical Applications

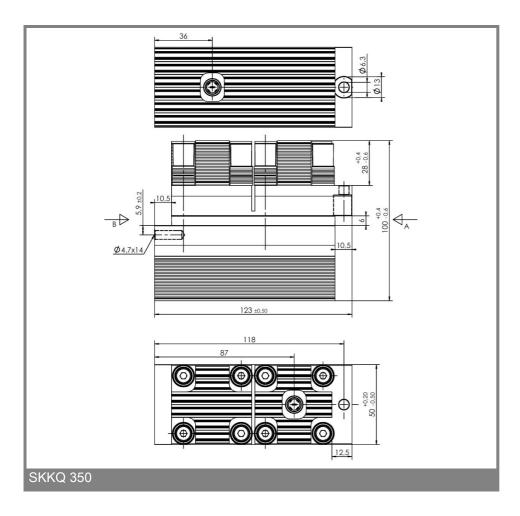
Soft Starters

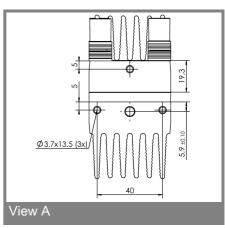
 T_{vjmax} up to 150°C is allowable for overload conditions, max. time period for the overload condition is 25s.

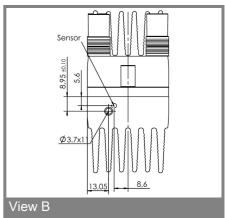
Absolute Maximum Ratings						
Symbol	Conditions	Values	Units			
I _{overload}	W1C; sin. 180°; 20 sec.; T _{vjmax.} = 150 °C; T _{vjstart} = 40°C	1225	Α			
I _{TSM}	$T_{vj} = 25^{\circ}C; 10 \text{ ms}$	9500	Α			
	$T_{vj} = 125^{\circ}C; 10 \text{ ms}$	8000	Α			
I²t	T _{vj} = 25°C; 8,3 10 ms	451000	A²s			
	T _{vj} = 125°C; 8,3 10 ms	320000	A²s			
SKKQ 350/14						
V _{RSM}		1500	V			
V_{RRM}, V_{DRM}		1400	V			
SKKQ 430/18						
V_{RSM}		1900	V			
V_{RRM}, V_{DRM}		1800	V			
T _{vj}		-40 +125 ¹⁾	°C			
T _{stg}		-40 + 125	°C			

Characteristics							
Symbol	Conditions	min.	typ.	max.	Units		
V_{T}	$T_{vi} = 25^{\circ}C; I_{T} = 1500 A$			1,65	V		
$V_{T(TO)}$	$T_{vj} = 125^{\circ}C$			0,9	V		
r _T	$T_{vj} = 125^{\circ}C$			0,5	mΩ		
$I_{DD};I_{RD}$	T_{vj} = 125°C; $V_{RD} = V_{RRM}$; per module			72	mA		
t_{gd}	$T_{vj} = 25^{\circ}C; I_{G} = 1A; di_{G}/dt = 1A/\mu s$		1		μs		
t _{gr}	$V_{D} = 0.67 * V_{DRM}$		2		μs		
(dv/dt) _{cr}	T _{vi} = 125°C		1000		V/µs		
(di/dt) _{cr}	T _{vi} = 125°C; f = 50 60 Hz		200		A/µs		
t _q	$T_{vi} = 125^{\circ}C$		150		μs		
I _H	$T_{vj} = 25^{\circ}C$		150	500	mA		
IL	$T_{vj} = 25^{\circ}C$; $R_G = 33 \Omega$		300	2000	mA		
V_{GT}	$T_{vj} = 25^{\circ}C; d.c.$	3			V		
I_{GT}	$T_{vj} = 25^{\circ}C; d.c.$	200			mA		
V_{GD}	$T_{vj} = 125^{\circ}C; d.c.$			0,25	V		
I_{GD}	$T_{vj} = 125^{\circ}C; d.c.$			10	mA		
R _{th(j-s)}	cont.; per thyristor			0,066	K/W		
M _t			5 ± 15%		Nm		
m	approx.		1200		g		
Case			SKKQ 350				









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